

Description

The present invention relates to a method of removing BCl_3 , Cl_2 , AlCl_3 , HCl or the like from waste gas discharged from chemical dry etching processes using chloride and/or chlorine containing gases in the semiconductor industry to thereby making these waste gases harmless.

It is feared that environmental pollution may be caused by a large variety of harmful gases which are used in semiconductor manufacturing processes in the semiconductor industry. Chloride and/or chlorine containing gases which are contained in waste gas discharged from chemical dry etching processes using chloride and/or chlorine containing gases are extremely harmful to the human body and therefore it is urgent to establish an effective system for removing such harmful components from the waste gas.

Various kinds of method of removing chloride and/or chlorine containing gases have heretofore been proposed. These known methods may be roughly divided into two types, that is, wet treating method and dry treating method.

In the wet treating method, waste gas and a cleaning solution which is generally an alkaline aqueous solution, e.g., NaOH , are brought into countercurrent contact with each other in a gas-liquid contact apparatus such as a packed tower or a spray tower to thereby neutralize and absorb harmful chloride and/or chlorine containing gases.

This type of treating method suffers, however, from the following problems: the cleaning solution may flow back to the etching equipment; the waste gas treating apparatus may be clogged with a reaction product; and the treating efficiency is low.

The dry treating method employs a solid treating agent to remove harmful waste gases, and there are two different types of dry treating method, that is, one that employs an agent carried on active carbon as a treating agent for chloride and/or chlorine containing gases [see Japanese Patent Public Disclosure Number 61-35849 (1986)], and the other that employs an alkaline treating agent alone, that is, without any carrier or the like [Japanese Patent Public Disclosure Number 61-61619 (1986)].

In the dry treating method, a treating agent is packed in a packed tower and waste gas is passed through the tower to remove harmful components from the waste gas. In this type of method, the operation is simpler and the system is simpler and smaller than in the case of the wet treating method, but the method suffers from the following problems.

The waste gas discharged from chemical dry etching processes using BCl_3 and Cl_2 contains at least two different kinds of chloride and chlorine containing gas, i.e., BCl_3 and Cl_2 .

When a gas mixture of BCl_3 and Cl_2 is treated by the dry method, BCl_3 and Cl_2 are adsorbed by the treating agent in different amounts, respectively. More specifically, in either case where a treating agent carried on active carbon is used or an alkaline agent alone is employed as a treating agent, the adsorptive capacity for either BCl_3 or Cl_2 is large, but that for the other is small.

For this reason, when dry etching waste gas is treated, if the load of a gas for which the adsorptive capacity of the treating agent is smaller is high, this gas breaks through in a relatively short period of time and therefore the cycle of replacement of the treating agent in the packed tower is shortened, which results in an increase in the amount of treating agent used.

In view of the above-described circumstances, it is a primary object of the present invention to provide a method of effectively removing by dry process a chloride and chlorine containing gas that contains at least BCl_3 and Cl_2 from a waste gas discharged from dry etching process or other manufacturing process in the semiconductor industry, the method enabling a reduction in the amount of treating agent used and permitting a lengthening of the cycle of replacement of the treating agent in the packed tower.

According to the invention a method of treating a waste gas containing at least boron trichloride and chlorine, comprises first treating the waste gas with a treating agent consisting of a magnesium compound packed in a tower and then treating said waste gas with a treating agent consisting of a calcium compound packed in the same or another tower, the temperature within said tower being in the range of from 20°C to 80°C , the waste gas being passed through said tower under a pressure of from 0.91×10^5 Pa (0.9 atm) to 2.03×10^5 Pa (2 atm) and the particle size of the treating agents being 0.3 mm to 5.0 mm in diameter, wherein said magnesium compound is selected from the group consisting of magnesium hydroxide, magnesium oxide, magnesium carbonate and a mixture thereof, while said calcium compound is selected from the group consisting of calcium hydroxide, calcium oxide, calcium carbonate and a mixture thereof.

The above and other objects, features and advantages of the present invention will become more apparent from the following description taken in conjunction with the accompanying drawing.

Fig. 1 is a schematic view of an apparatus employed to evaluate the performance of the treating agents used in the present invention.

Examples of chloride and/or chlorine containing gases contained in a dry etching waste gas or the like

which is to be treated in the present invention include BCl_3 , Cl_2 , AlCl_3 , HCl , etc. The present invention is effectively applied to a waste gas that contains at least BCl_3 and Cl_2 which are mixed in an arbitrary ratio.

The waste gas generally has a flow rate of from several to tens l/min and contains about 0.1 to 10% by volume of BCl_3 , and Cl_2 , respectively. The temperature and pressure of the waste gas vary depending on the various constructional aspects of the exhaust system of the exhaust pump used, the exhaust duct, etc. and generally may be about 20 - 80°C and about $1.01 - 2.03 \times 10^5$ Pa (1 - 2 atm), respectively.

Examples of treating agents usable in the present invention are magnesium hydroxide, magnesium oxide and magnesium carbonate as magnesium compounds and slaked lime, calcium oxide and calcium carbonate as calcium compounds. These compounds may be carried on appropriate carriers.

These compounds may be used in the form of fragments, tablets, granules, etc. The particle size may be chosen arbitrarily depending on the flow rate of the waste gas and the dimensions of the tower in which the treating agent is packed, and with a view to maximizing the treatment efficiency, it may preferably be in the range of about 0.3 - 5.0 mm in a diameter.

When each of the magnesium compounds in the above-described treating agents was brought into contact with a gas containing either BCl_3 , or Cl_2 and a gas mixture containing both of them, the adsorptive capacity for BCl_3 was large, but that for Cl_2 was extremely small. When each of the calcium compounds was brought into contact with either BCl_3 or Cl_2 , both the adsorptive capacities for the two different kinds of gas were large. However, when it was brought into contact with a gas mixture containing both BCl_3 and Cl_2 , the adsorptive capacity for BCl_3 was large, but that for Cl_2 was extremely small.

Therefore, it was revealed that, to remove a gas mixture that contains BCl_3 , and Cl_2 , it is impossible to obtain a sufficient treating effectiveness simply by employing one kind of treating agent, that is, either a magnesium or calcium compound, and it is most appropriate to use a combination of these two different kinds of treating agent.

More specifically, the present inventors have found that a gas mixture containing BCl_3 and Cl_2 can be removed considerably effectively by first removing BCl_3 with a magnesium compound and then removing with a calcium compound the residual Cl_2 which was not removed with the magnesium compound. The present invention has been accomplished on the basis of this finding.

The waste gas and the treating agents may be brought into contact with each other by the following means. A magnesium compound and a calcium compound are packed in a packed tower in two series stages, respectively, in the required proportion, and waste gas is passed either upward or downward through the packed tower so that the gas is successively brought into contact with the magnesium and calcium compounds in the mentioned order.

Hereinunder, the present invention will be described more specifically by way of examples. However, the present invention is in no way restricted by these examples.

Example 1:

As magnesium and calcium compounds serving as two treating agents, granulated magnesium hydroxide (particle diameter: 0.42 to 0.50 mm) and granulated slaked lime (particle diameter: 0.42 to 0.50 mm) were employed.

Each of the above-described treating agents was packed in a quartz column 1 (height: 400 mm; diameter: 40 mm) of an experimental apparatus such as that shown in Fig. 1. N_2 gases having the following various compositions were supplied to the column 1 from the lower side thereof through an inlet pipe 2: N_2 gas containing N_2 (0.30 l/min) and BCl_3 (0.01 l/min); N_2 gas containing N_2 (0.28 l/min) and Cl_2 (0.03 l/min); and N_2 gas containing N_2 (0.27 l/min), BCl_3 (0.01 l/min) and Cl_2 (0.03 l/min). The amount of each of BCl_3 and Cl_2 absorbed until both BCl_3 and Cl_2 in the waste gas in the outlet pipe 3 at the upper side of the column 1 up to 1 ppm was measured. The gas to be treated was at ambient temperature and was supplied to the column at the atmosphere plus about 20 mm H_2O (2.97×10^5 Pa).

The results are shown in Table 1 below.

Table 1

Treating agents	BCl ₃ adsorbing capacity (Nl/kg)		Cl ₂ adsorbing capacity (Nl/kg)	
	BCl ₃ alone	BCl ₃ and Cl ₂	Cl ₂ alone	Cl ₂ and BCl ₃
Magnesium hydroxide	66	52	1.0	0.7
Slaked lime	23	18	88	8.0

As will be clear from Table 1, as to the effectiveness in removing BCl₃, magnesium hydroxide is higher than slaked lime and also has a high adsorptive capacity, i.e., 52 Nl/kg, in the treatment of the gas mixture containing both BCl₃ and Cl₂. As to Cl₂, magnesium hydroxide can remove substantially no Cl₂, whereas slaked lime has high removing capability. However, the Cl₂ adsorbing capacity of slaked lime for a gas mixture containing both BCl₃ and Cl₂ is considerably low, i.e., 10% of that in the case of treatment of a waste gas containing Cl₂ alone as a harmful component. Accordingly, it may be considered that, to remove a gas mixture that contains BCl₃ and Cl₂, it is impossible to obtain a sufficient treating effectiveness simply by employing one kind of treating agent, that is, either a magnesium or calcium compound, and it is most appropriate to use a combination of these two different kinds of treating agent.

Example 2:

An experiment was conducted in order to confirm the waste gas treating effectiveness of the combination of two different kinds of treating agent. With the same treating agents and the same experimental apparatus as in Example 1, 100 g of magnesium hydroxide was packed in the lower stage of the column, and 100 g of slaked lime in the upper stage in series to the lower stage. N₂ gases were treated under the same gas mixture conditions as in Example 1 to measure the amounts of BCl₃ and Cl₂ absorbed. The results are shown in Table 2 below.

Table 2

Treating agents	BCl ₃ adsorbing capacity (Nl/kg)	Cl ₂ adsorbing capacity (Nl/kg)
Magnesium hydroxide	50	-
Slaked lime	-	70

The experiment has revealed that magnesium hydroxide has a BCl₃ adsorbing capacity of 50 Nl/kg, while slaked lime has a Cl₂ adsorbing capacity of 70 Nl/kg, that is, it is possible to obtain harmful gas removing effectiveness as high as that in the case of treating BCl₃ or Cl₂ alone.

As has been described above, the present invention enables a chloride and chlorine containing gas that contains at least BCl₃ and Cl₂ to be efficiently removed from waste gas discharged from dry etching

process or other manufacturing process in the semiconductor industry. In addition, it is possible according to the present invention to reduce the amount of treating agent used, lengthen the treating agent replacing cycle, and facilitate the maintenance of the system.

5 Claims

1. A method of treating a waste gas containing at least boron trichloride and chlorine, comprising first treating the waste gas with a treating agent consisting of a magnesium compound packed in a tower and then treating said waste gas with a treating agent consisting of a calcium compound packed in the same or another tower, the temperature within said tower being in the range of from 20 °C to 80 °C, the waste gas being passed through said tower under a pressure of from 0.91×10^5 Pa to 2.03×10^5 Pa and the particle size of the treating agents being 0.3 mm to 5.0 mm in diameter, wherein said magnesium compound is selected from the group consisting of magnesium hydroxide, magnesium oxide, magnesium carbonate and a mixture thereof, while said calcium compound is selected from the group consisting of calcium hydroxide, calcium oxide, calcium carbonate and a mixture thereof.
2. The method of Claim 1 or 2, wherein said waste gas is discharged from a chemical dry etching step using a chloride and/or chlorine containing gas in a semiconductor manufacturing process.

20 Patentansprüche

1. Verfahren zum Behandeln von Abgas, das zumindest Bortrichlorid und Chlor enthält, wobei das Verfahren folgendes aufweist: Zuerst Behandeln des Abgases mit einem Behandlungsmittel, das aus einer Magnesiumverbindung besteht und in einen Turm gepackt ist und dann Behandeln des Abgases mit einem Behandlungsmittel, das aus einer Kalziumverbindung besteht und in den gleichen oder einen anderen Turm gepackt ist, wobei die Temperatur innerhalb des Turms im Bereich von 20 °C bis 80 °C ist, wobei das Abgas durch den Turm unter einem Druck von $0,91 \times 10^5$ bis $2,03 \times 10^5$ Pa geleitet wird und wobei die Partikelgröße des Behandlungsmittels 0,3 mm bis 5,0 mm im Durchmesser ist, wobei die Magnesiumverbindung ausgewählt ist aus der Gruppe, die aus Magnesiumhydroxid, Magnesiumoxid, Magnesiumkarbonat und einer Mischung daraus besteht, wogegen die Kalziumverbindung ausgewählt ist aus der Gruppe, die aus Kalziumhydroxid, Kalziumoxid, Kalziumkarbonat und einer Mischung daraus besteht.
2. Verfahren nach Anspruch 1, wobei das Abgas abgelassen wird aus einem chemischen Trockenätzschritt, der ein chlorid- und/oder chlorethaltendes Gas verwendet, und zwar in einem Halbleiter-Herstellungsprozeß.

Revendications

1. Procédé de traitement d'un gaz usé contenant au moins du trichlorure de bore et du chlore, selon lequel on traite d'abord le gaz usé avec un agent de traitement consistant en un composé du magnésium incorporé dans une tour, et on traite ensuite ce gaz usé avec un agent de traitement consistant en un composé du calcium introduit dans la même ou une autre tour, la température dans cette tour étant de 20 °C à 80 °C, le gaz usé étant mis en circulation à travers la tour sous une pression de $0,91 \times 10^5$ Pa à $2,03 \times 10^5$ Pa et la taille particulière des agents de traitement étant de 0,3 mm à 5,0 mm de diamètre, et selon lequel le composé du magnésium est choisi parmi l'hydroxyde de magnésium, l'oxyde de magnésium, le carbonate de magnésium et un mélange de ceux-ci, tandis que le composé du calcium est choisi parmi l'hydroxyde de calcium, l'oxyde de calcium, le carbonate de calcium et un mélange de ceux-ci.
2. Procédé selon la revendication 1, dans lequel le gaz usé est évacué à partir d'une opération d'attaque chimique à sec mettant en oeuvre un gaz contenant des chlorures et/ou du chlore, d'un procédé de fabrication de semi-conducteurs.

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